

STPS3L60S

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

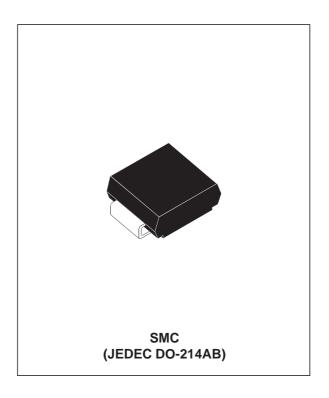
I _{F(AV)}	3 A
V _{RRM}	60 V
Tj (max)	150°C
V _F (max)	0.65 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Schottky rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters. Packaged in SMC, this device is intended for use in DC/DC chargers.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	60	V
I _{F(RMS)}	RMS forward current	10	Α
I _{F(AV)}	Average forward current	3	Α
I _{FSM}	Surge non repetitive forward current	75	Α
I _{RRM}	Repetitive peak reverse current	1	Α
P _{ARM}	Repetitive peak avalanche power	1600	W
T _{stg}	Storage temperature range	- 65 to + 175	°C
Tj	Maximum operating junction temperature *	150	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs

* :
$$\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$$
 thermal runaway condition for a diode on its own heatsink

July 2003 - Ed: 2A

STPS3L60S

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-l)}	Junction to leads	20	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage current	Tj = 25°C	$V_R = V_{RRM}$			55	μA
		Tj = 125°C			10	15	mA
V _F *	Forward voltage drop	Tj = 25°C	I _F = 3 A			0.7	V
		Tj = 125°C	I _F = 3 A		0.56	0.65	
		Tj = 25°C	I _F = 6 A			0.94	
		Tj = 125°C	I _F = 6 A		0.67	0.76	

Pulse test : * tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation : P = 0.54 x $I_{F(AV)}$ + 0.037 $I_{F}^{\,2}_{(RMS)}$

Fig. 1: Average forward power dissipation versus average forward current.

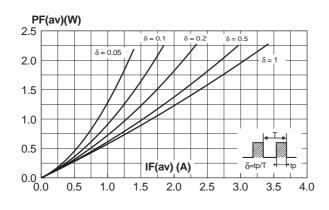
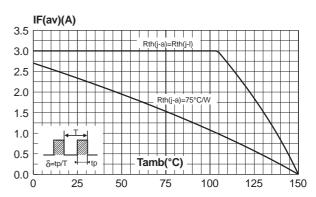


Fig. 2: Average forward current versus ambient temperature($\delta = 0.5$).



57 2/5

Fig. 3: Normalized avalanche power derating versus pulse duration.

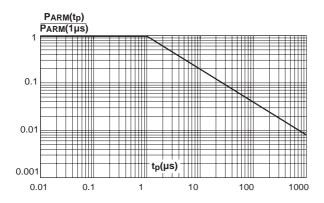


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

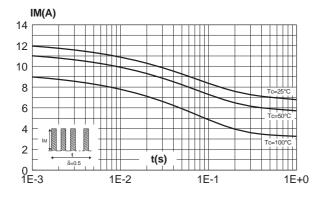


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

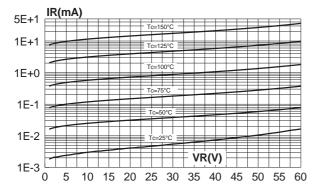


Fig. 4: Normalized avalanche power derating versus junction temperature.

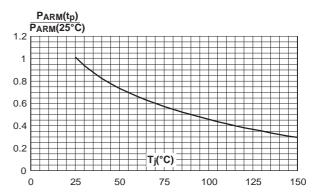


Fig. 6: Relative variation of thermal impedance junction to lead versus pulse duration.

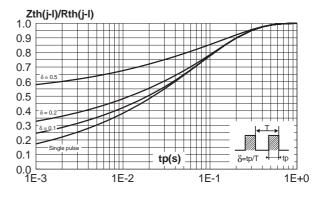
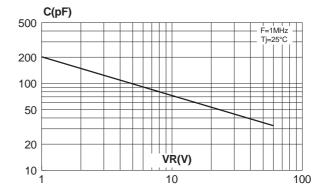


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).



 $\overline{\Delta}$

Fig. 9-1: Forward voltage drop versus forward current (low level, maximum values).

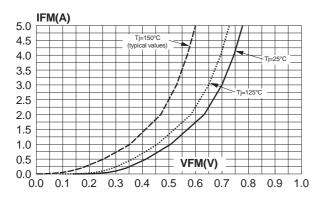


Fig. 10: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy

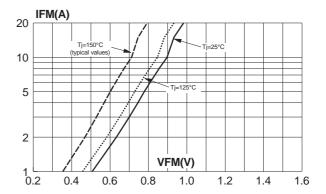
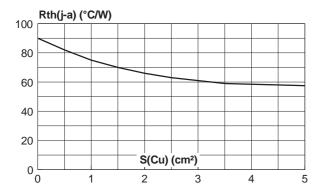


Fig. 9-2: Forward voltage drop versus forward

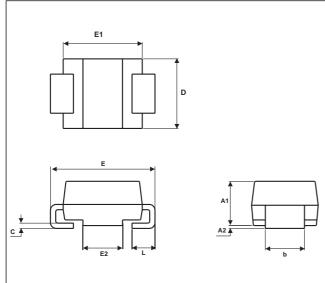
current (high level, maximum values).

printed circuit board FR4, copper thickness: 35µm)



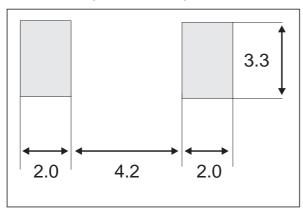
4/5

PACKAGE MECHANICAL DATA



	DIMENSIONS				
REF.	REF. Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.096	
A2	0.05	0.20	0.002	0.008	
b	2.90	3.2	0.114	0.126	
С	0.15 0.41		0.006	0.016	
Е	7.75	8.15	0.305	0.321	
E1	6.60	7.15	0.260	0.281	
E2	4.40	4.70	0.173	0.185	
D	5.55	6.25	0.218	0.246	
L	0.75	1.60	0.030	0.063	

FOOT PRINT (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3L60S	S36	SMC	0.24g	2500	Tape and reel

■ EPOXY MEETS UL94,V0

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written

approval of STMicroelectronics

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany

Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore

Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com